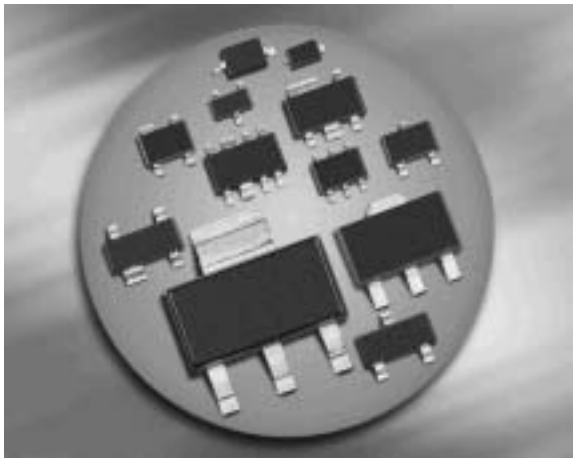
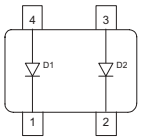
Silicon Switching Diode

- For high-speed switching applications
- Electrical insulated diodes
- Pb-free (RoHS compliant) package[1)]
- Qualified according AEC Q101



BAS28/W



Type	Package	Configuration	Marking
BAS28	SOT143	parallel pair	JTs
BAS28W	SOT343	parallel pair	JTs

Maximum Ratings at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Peak reverse voltage	V_{RM}	85	
Forward current	I_F	200	mA
Peak forward current	I_{FM}	-	
Surge forward current, t = 1 µs	I_{FS}	4.5	A
Non-repetitive peak surge forward current	I_{FSM}	-	
Total power dissipation BAS28, $T_S \leq$ 31°C BAS28W, $T_S \leq$ 103°C	P_{tot}	 330 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ... 150	

[1]Pb-containing package may be available upon special request

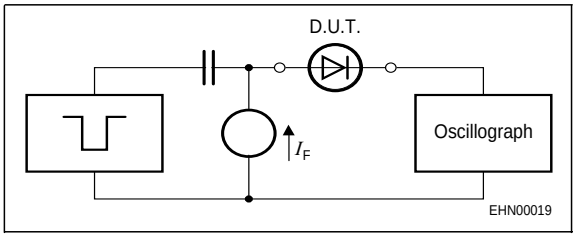
Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}		K/W
BAS28		≤ 360	
BAS28W		≤ 190	

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)}$ = 100 µA	$V_{(BR)}$	85	-	-	V
Reverse current	I_R				µA
V_R = 75 V		-	-	0.1	
V_R = 25 V, T_A = 150 °C		-	-	30	
V_R = 75 V, T_A = 150 °C		-	-	50	
Forward voltage	V_F				mV
I_F = 1 mA		-	-	715	
I_F = 10 mA		-	-	855	
I_F = 50 mA		-	-	1000	
I_F = 100 mA		-	-	1200	
I_F = 150 mA		-	-	1250	
AC Characteristics					
Diode capacitance V_R = 0 V, f = 1 MHz	C_T	-	-	2	pF
Reverse recovery time I_F = 10 mA, I_R = 10 mA, measured at I_R = 1mA , R_L = 100 Ω	t_{rr}	-	-	4	ns

Test circuit for reverse recovery time



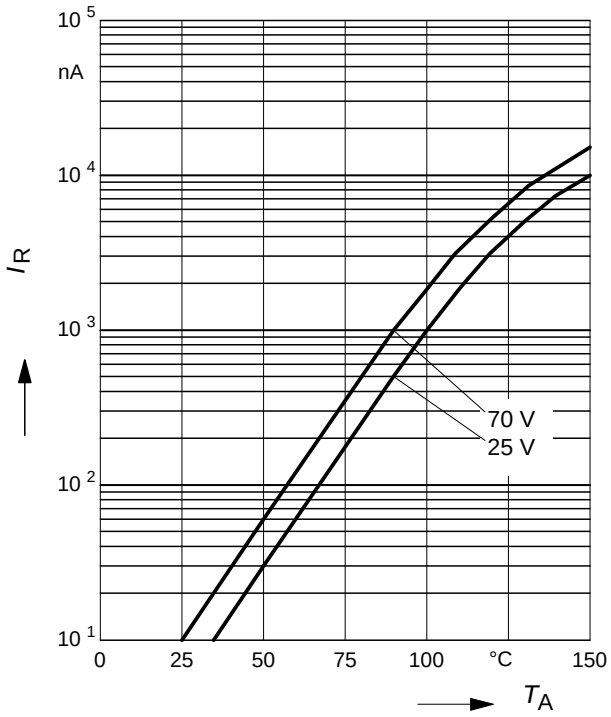
Pulse generator: t_p = 100ns, D = 0.05,
t_r = 0.6ns, R_i = 50Ω

Oscillograph: R = 50Ω, t_r = 0.35ns,
C ≤ 1pF

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

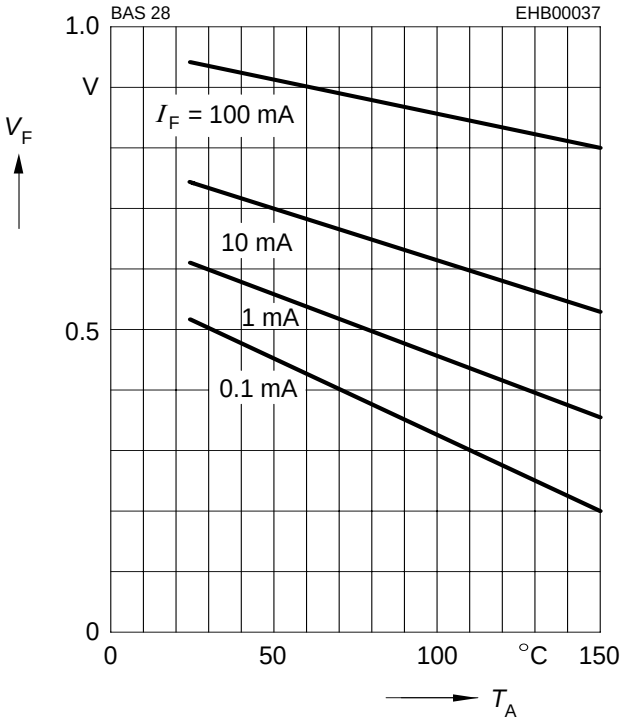
Reverse current $I_R = f(T_A)$

V_R = Parameter



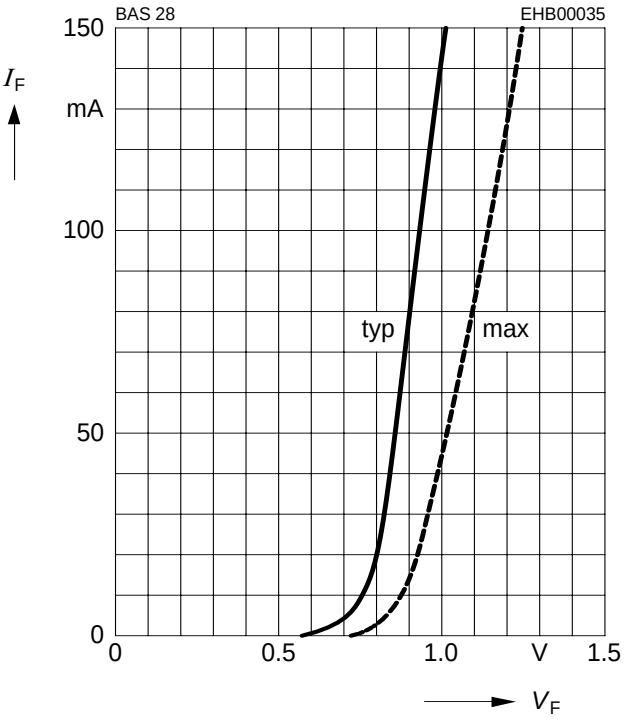
Forward Voltage $V_F = f(T_A)$

I_F = Parameter



Forward current $I_F = f(V_F)$

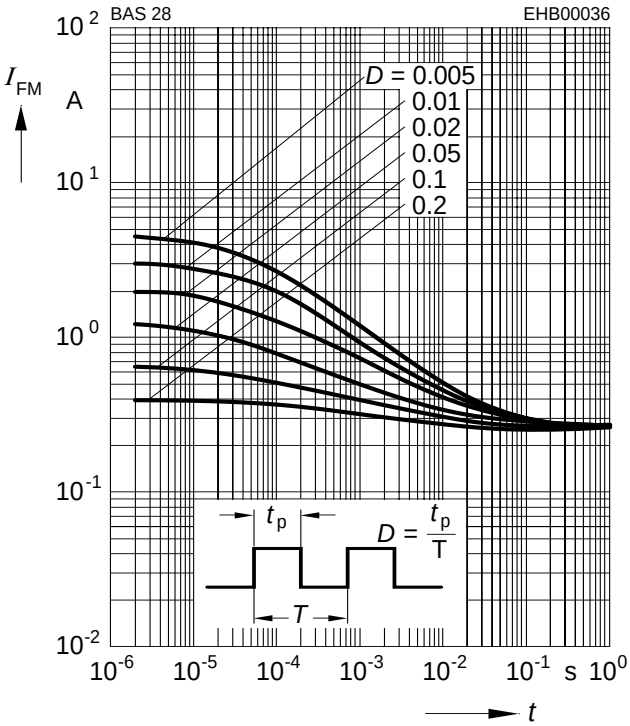
T_A = 25 °C



Peak forward current $I_{FM} = f(t_p)$

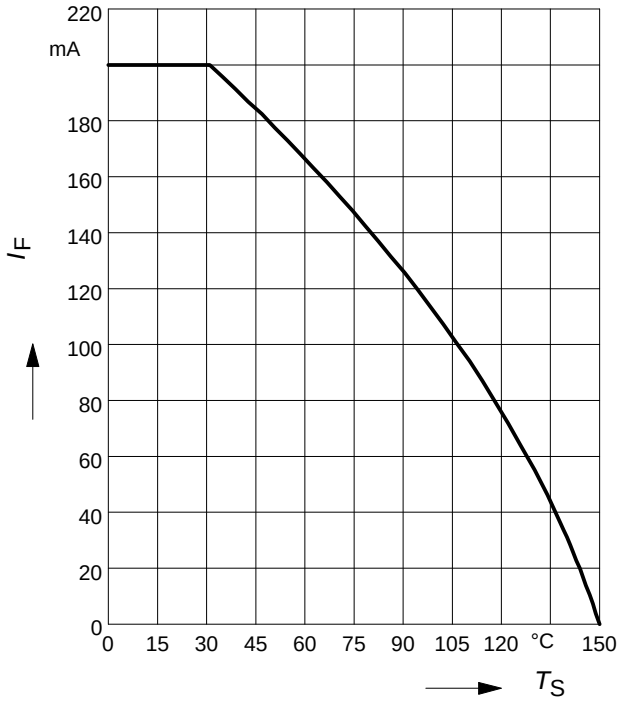
T_A = 25 °C

BAS28



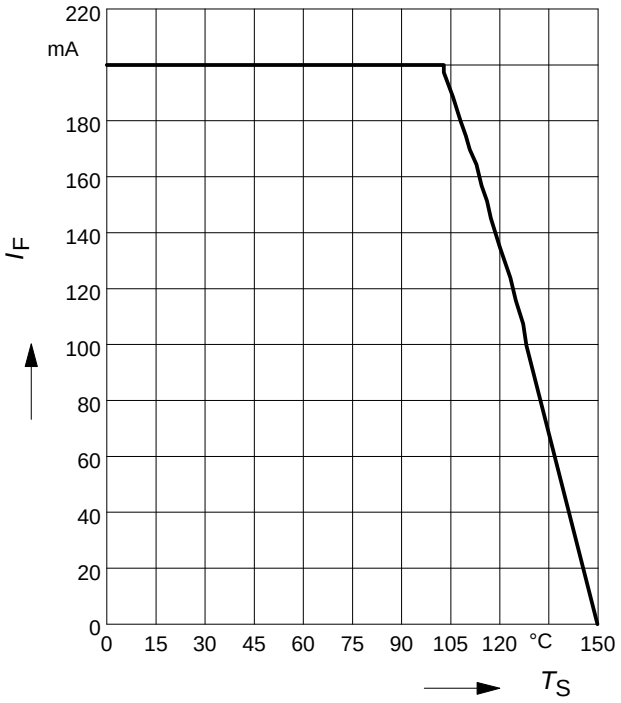
Forward current $I_F = f(T_S)$

BAS28



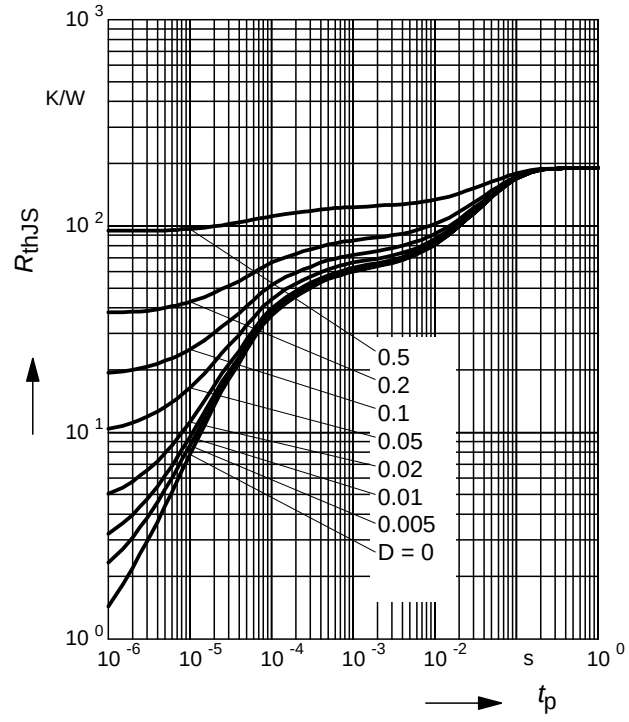
Forward current $I_F = f(T_S)$

BAS28W



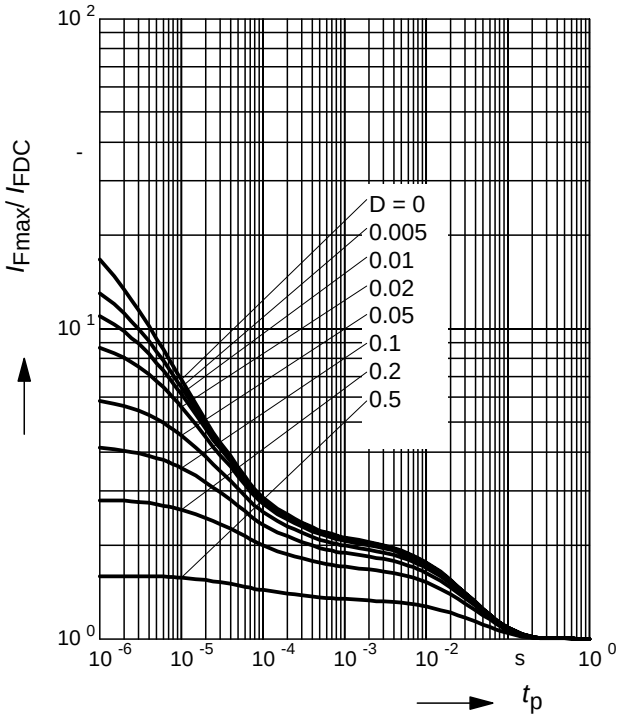
Permissible Puls Load $R_{thJS} = f(t_p)$

BAS28W

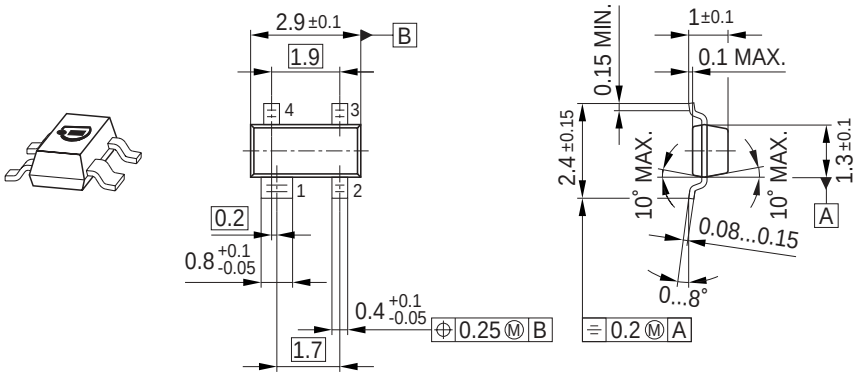


Permissible Pulse Load

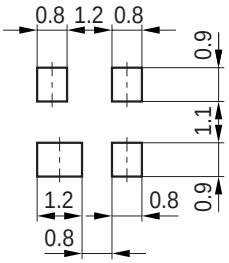
$I_{Fmax}/ I_{FDC} = f(t_p)$ BAS28W



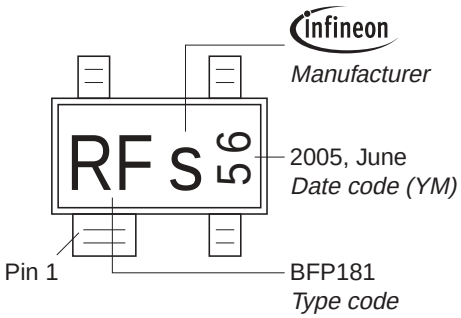
Package Outline



Foot Print

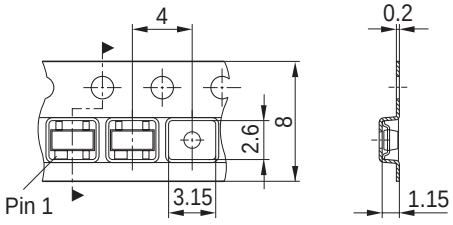


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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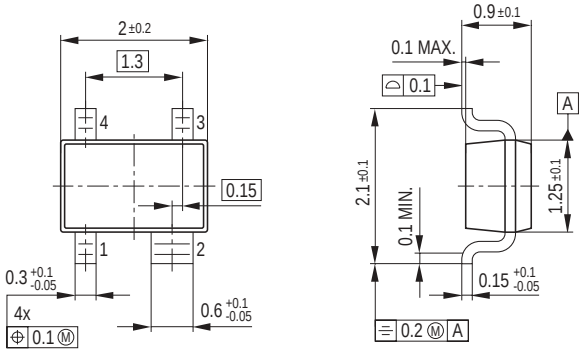

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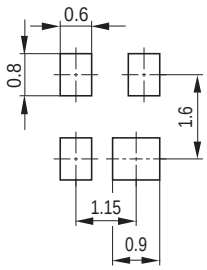
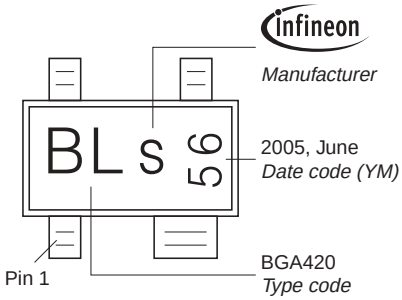


Marking Layout (Example)



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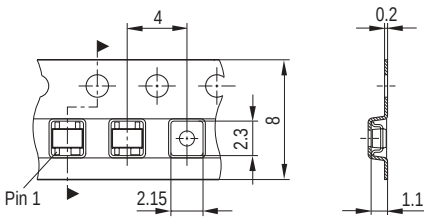

Edition 2006-02-01
Published by
Infineon Technologies AG
81726 München, Germany
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